

Certificate of Analysis (CoA)

Dec. 25, 2025

Product Name: Indium Tin Oxide (ITO) Sputtering Target**Chemical Formula:** $\text{In}_2\text{O}_3 \cdot \text{SnO}_2$ **Composition:** 90 wt% In_2O_3 / 10 wt% SnO_2 **Purity:** 99.99% (4N, oxide basis)**Dimensions:** $\varnothing 76.2 \text{ mm} \times 1.59 \text{ mm}$ **Bonding:** Indium-bonded to Copper (Cu) Backing Plate, 1.59 mm thick**Lot Number:** CSFM-251225086TB**Quantity:** 1 piece**Manufactured by:** Thin-Film Materials

Physical Description

- Form: Oxide ceramic sputtering target, bonded
- Appearance: Grayish-yellow, dense ceramic
- Crystal Structure: Cubic bixbyite (In_2O_3 structure with Sn doping)
- Theoretical Density: $\sim 7.1 \text{ g/cm}^3$
- Resistivity: $< 5.0 \times 10^{-4} \Omega \cdot \text{cm}$ (for sintered target)
- Fabrication: Powder synthesis, pressing, sintering, precision grinding, and bonding

Total Impurities (by ICP-OES / GDMS)

Element	Symbol	Max. Content (ppm)
In_2O_3, SnO_2	In, Sn	Balance (>99.99%)
Lead	Pb	< 5
Iron	Fe	< 5
Silicon	Si	< 5
Aluminum	Al	< 5
Zinc	Zn	< 5
Copper	Cu	< 5

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Element	Symbol	Max. Content (ppm)
Other Metallic (each)	-	< 2

Handling & Storage

- This is a brittle ceramic material. Handle with care to avoid chipping or cracking.
- Store in a dry, clean environment to prevent moisture absorption and contamination.
- Avoid thermal shock.

Declaration

We certify that this ITO target meets the specified composition and 4N purity, ensuring consistent performance for depositing highly transparent and conductive thin films in display, touch panel, and photovoltaic applications.

Authorized Signature:Inspection Certificate by: Nancy LiuApprover by: Chen Qiang